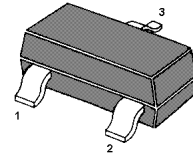


MMBT4401

NPN Silicon General Purpose Transistor

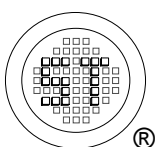


1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current Continuous	I_C	600	mA
Total Device Dissipation FR-5 Board ¹⁾ Derate above 25 °C	P_{tot}	200 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

¹⁾ FR-5 = 1 X 0.75 X 0.062 in.



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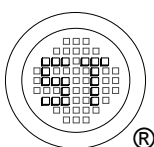


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Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 0.1\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 1\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 10\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 150\text{ mA}$ at $V_{CE} = 2\text{ V}$, $I_C = 500\text{ mA}$	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	20 40 80 100 40	- - - 300 -	- - - - -
Collector Base Cutoff Current at $V_{CB} = 35\text{ V}$	I_{CBO}	-	0.1	μA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	0.1	μA
Collector Base Breakdown Voltage at $I_C = 0.1\text{ mA}$	$V_{(BR)CBO}$	60	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $I_E = 0.1\text{ mA}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$ $V_{CE(sat)}$	- -	0.4 0.75	V V
Base Emitter Saturation Voltage at $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$ $V_{BE(sat)}$	0.75 -	0.95 1.2	V V
Current Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$, $f = 100\text{ MHz}$	f_T	250	-	MHz
Collector Base Capacitance at $V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6.5	pF
Delay Time $V_{CC} = 30\text{ V}$, $V_{EB} = 2\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = 15\text{ mA}$	t_d	-	15	ns
Rise Time $V_{CC} = 30\text{ V}$, $V_{EB} = 2\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = 15\text{ mA}$	t_r	-	20	ns
Storage Time $V_{CC} = 30\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = I_{B2} = 15\text{ mA}$	t_s	-	225	ns
Fall Time $V_{CC} = 30\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = I_{B2} = 15\text{ mA}$	t_f	-	30	ns



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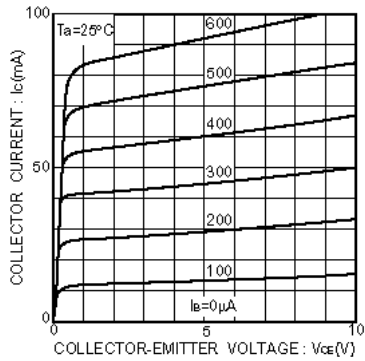


Fig.1 Grounded emitter output characteristics

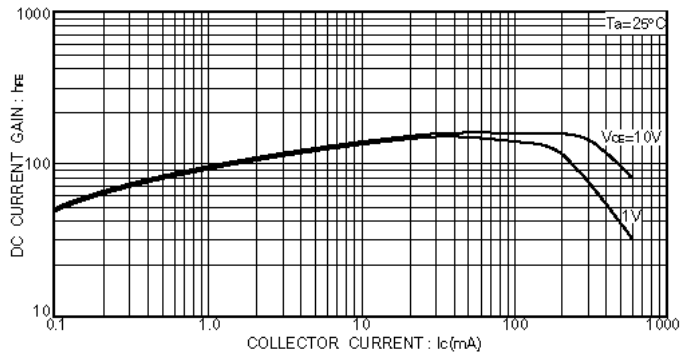


Fig.3 DC current gain vs. collector current(I)

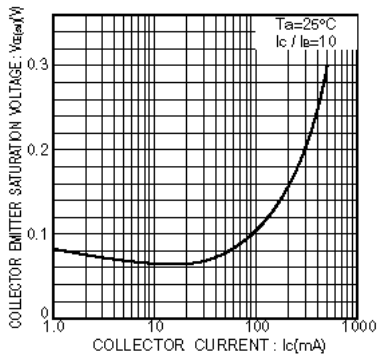


Fig.2 Collector-emitter saturation voltage vs. collector current

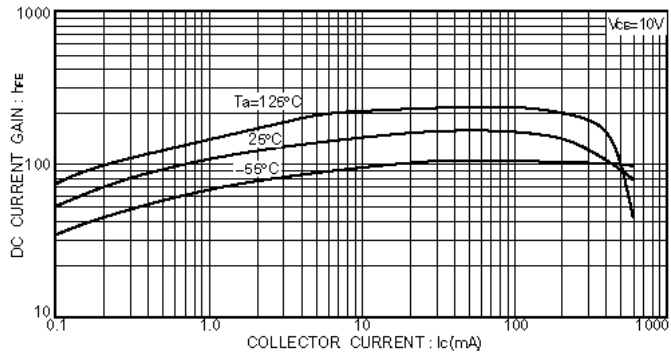


Fig.4 DC current gain vs. collector current(II)

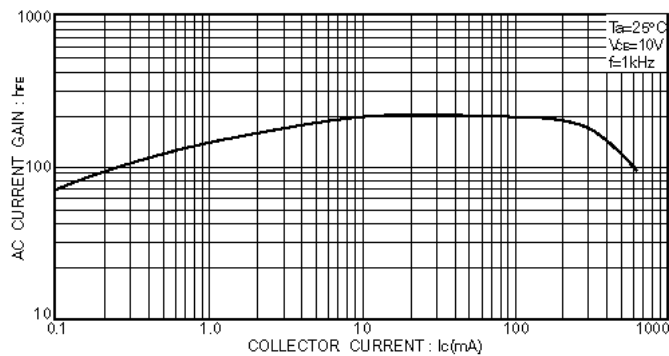


Fig.5 AC current gain vs. collector current

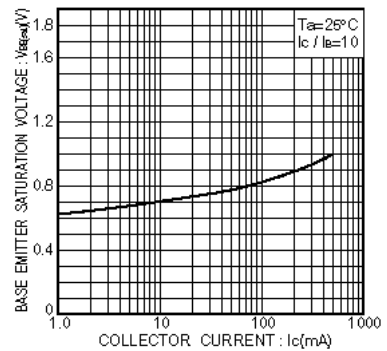
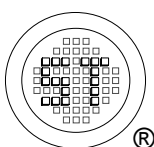


Fig.6 Base-emitter saturation voltage vs. collector current



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